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Mechanistic and In Situ Studies; References
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ReferencesChapter 6: Low-Temperature Atomic Layer Deposition; 6.1 Introduction; 6.2 Challenges of LT-ALD; 6.3 Materials and Processes; 6.4 Toward Novel LT-ALD Processes; 6.5 Thin Film Gas Diffusion Barriers; 6.6 Encapsulation of Organic Electronics; 6.7 Conclusions; Acknowledgments; References; Chapter 7: Plasma Atomic Layer Deposition; 7.1 Introduction; 7.2 Plasma Basics; 7.3 Plasma ALD Configurations; 7.4 Merits of Plasma ALD; 7.5 Challenges for Plasma ALD; 7.6 Concluding Remarks and Outlook; Acknowledgments; References; Part Two: Nanostructures by ALD
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10.3 Characterization Methods for ALD Coatings in High Aspect Ratio Structures

Sommario/riassunto

Atomic layer deposition, formerly called atomic layer epitaxy, was developed in the 1970s to meet the needs of producing high-quality, large-area fl at displays with perfect structure and process controllability. Nowadays, creating nanomaterials and producing nanostructures with structural perfection is an important goal for many applications in nanotechnology. As ALD is one of the important techniques which offers good control over the surface structures created, it is more and more in the focus of scientists. The book is structured in such a way to fi t both the need of the expert reader (du